

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	4.0	Secondary Flat Length	None or SEMI Standard	Wafer Vendor
	5.0	Overall Thickness	423.00 +/- 11.15 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<70.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<70.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	none	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	400.00 +/- 10.00 µm	ADE, 100%
	14.0	Handle Doping Type	Any	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	1 ~ 30 Ohm cm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide, laser mark, and light handling marks	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	30,000.00 +/- 3,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	21.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	22.0	Nominal Thickness	20.00 +/- 1.00 µm	Filmetrics 9 point, 100%
	23.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	24.0	Edge Removal Depth in Handle	<100um	Guaranteed by process
	25.0	Device Doping Type	Any	Wafer Vendor
	26.0	Device Dopant	Any	Wafer Vendor
	27.0	Device Growth Method	CZ	Wafer Vendor
	28.0	Device Resistivity	1 ~ 30 Ohm cm	Wafer Vendor
	29.0	Voids	none	Bright Light, 100% (note 2)
	30.0	Scratches	none	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method
----------	-----------	---------------	--------------------

Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information